



9NM65-VS

Power MOSFET

9A, 650V N-CHANNEL SUPER-JUNCTION MOSFET

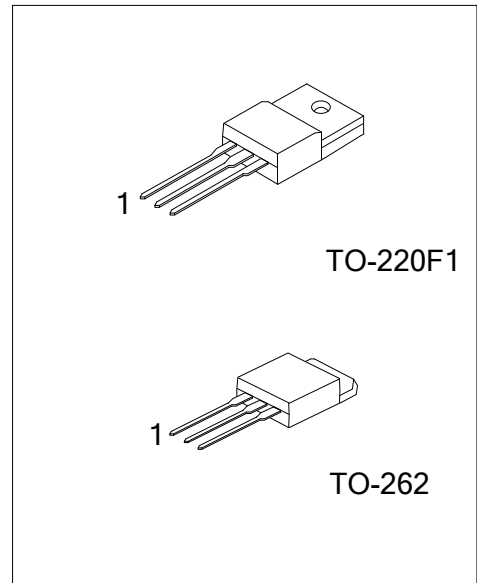
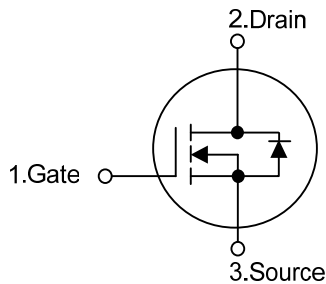
■ DESCRIPTION

The **UTC 9NM65-VS** is a Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristics. This power MOSFET is usually used at DC-DC, AC-DC converters for power applications.

■ FEATURES

- * $R_{DS(ON)} < 0.62 \Omega @ V_{GS} = 10V, I_D = 4.5A$
- * Fast Switching Capability
- * Avalanche Energy Tested
- * Improved dv/dt Capability, High Ruggedness

■ SYMBOL



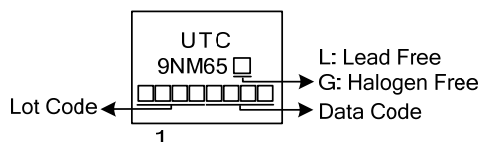
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen-Free		1	2	3	
9NM65L-TF1-T	9NM65G-TF1-T	TO-220F1	G	D	S	Tube
9NM65L-T2Q-T	9NM65G-T2Q-T	TO-262	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>9NM65G-TF1-T</p> <p>(1)Packing Type (2)Package Type (3)Green Package</p>	<p>(1) T: Tube (2) TF1: TO-220F1, T2Q: TO-262 (3) G: Halogen Free and Lead Free, L: Lead Free</p>
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■ MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	650	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	Continuous	I_D	9	A
	Pulsed (Note 2)	I_{DM}	20	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	157	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4	V/ns
Power Dissipation	TO-220F1	P_D	28	W
	TO-262		83	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $L=65\text{mH}$, $I_{AS}=2.2\text{A}$, $V_{DD}=50\text{V}$, $R_G=25\ \Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD}\leq 9.0\text{A}$, $di/dt\leq 200\text{A}/\mu\text{s}$, $V_{DD}\leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

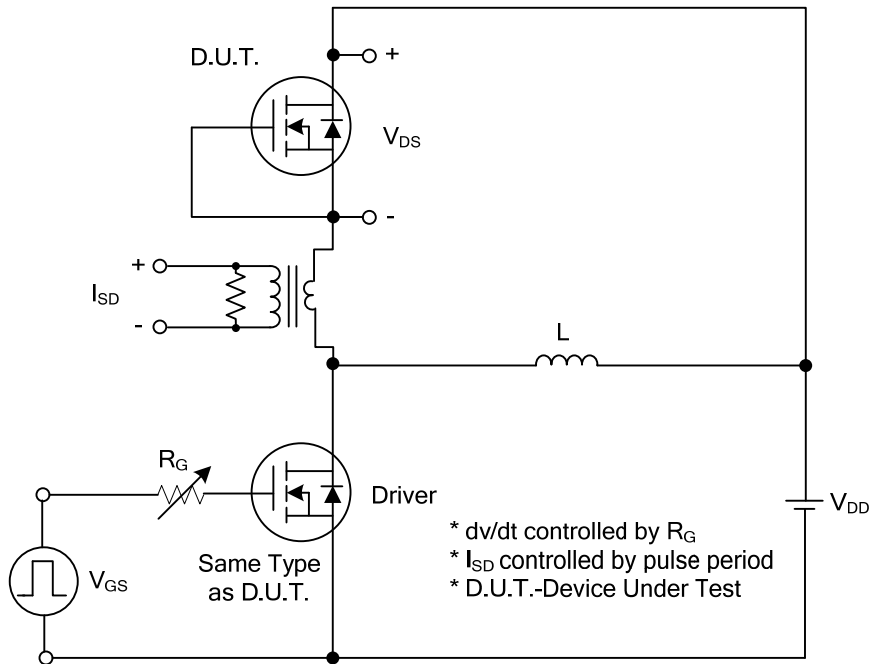
PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient		θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
Junction to Case	TO-220F1	θ_{JC}	4.5	$^\circ\text{C}/\text{W}$
	TO-262		1.5	$^\circ\text{C}/\text{W}$

■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

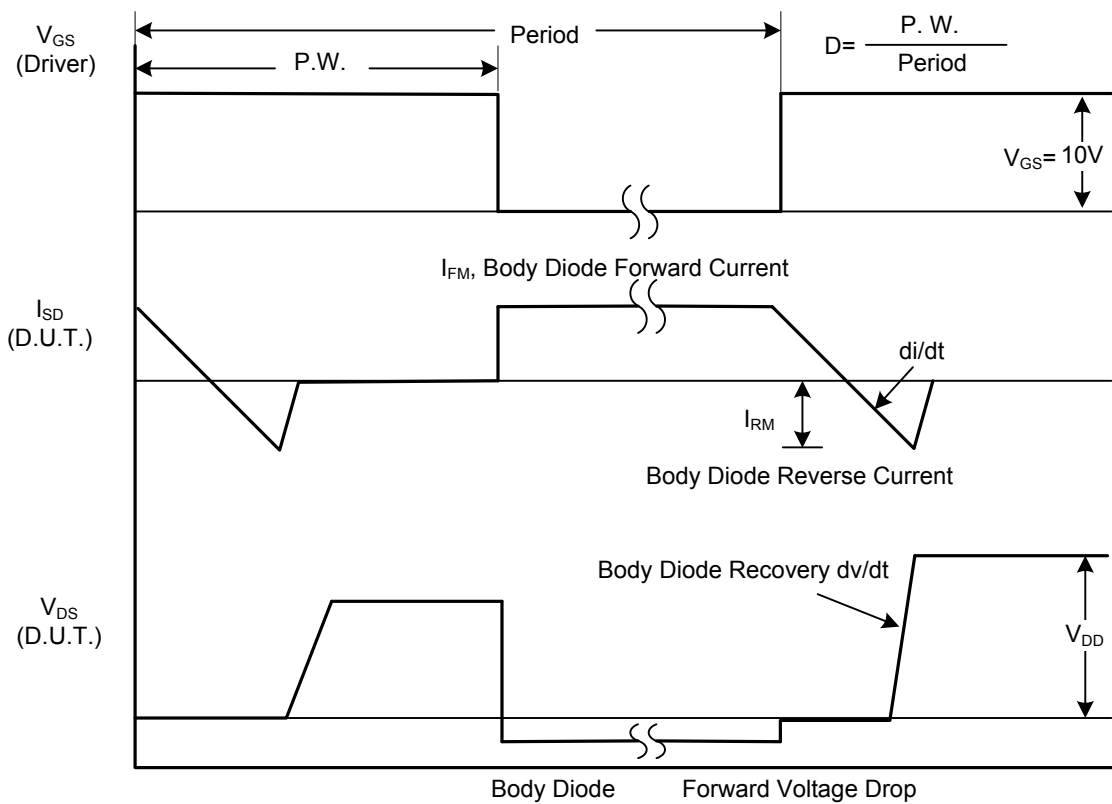
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV _{DSS}	V _{GS} = 0V, I _D = 250μA	650			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} = 650V, V _{GS} = 0V			10	μA
Gate- Source Leakage Current	Forward	I _{GSS}	V _{GS} = 30V, V _{DS} = 0V			100	nA
	Reverse		V _{GS} = -30V, V _{DS} = 0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} = V _{GS} , I _D = 250μA	2.0		4.0	V
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} = 10V, I _D = 4.5A			0.62	Ω
DYNAMIC CHARACTERISTICS							
Input Capacitance		C _{ISS}	V _{GS} =0V, V _{DS} =25V, f=1.0 MHz		620		pF
Output Capacitance		C _{OSS}			480		pF
Reverse Transfer Capacitance		C _{RSS}			38		pF
SWITCHING CHARACTERISTICS							
Total Gate Charge (Note 1)		Q _G	V _{DS} =300V, V _{GS} =10V, I _D =1.5A, I _G =2mA (Note 1, 2)		26.2		nC
Gate to Source Charge		Q _{GS}			3.5		nC
Gate to Drain Charge		Q _{GD}			9.8		nC
Turn-ON Delay Time (Note 1)		t _{D(ON)}	V _{DD} =100V, V _{GS} =10V, I _D =1.0A, R _G =25Ω (Note 1, 2)		8		ns
Rise Time		t _R			20		ns
Turn-OFF Delay Time		t _{D(OFF)}			100		ns
Fall-Time		t _F			48		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I _S				9	A
Maximum Body-Diode Pulsed Current		I _{SM}				36	A
Drain-Source Diode Forward Voltage (Note 1)		V _{SD}	I _S =9.0A, V _{GS} =0V			1.4	V
Body Diode Reverse Recovery Time (Note 1)		t _{rr}	I _S =9.0A, V _{GS} =0V, di _F /dt=100A/μs		234		ns
Body Diode Reverse Recovery Charge		Q _{rr}			2		μC

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.
 2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

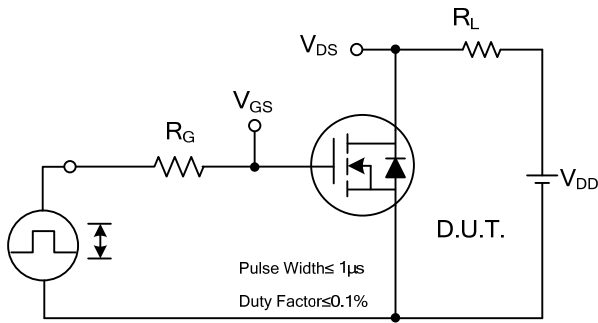


Peak Diode Recovery dv/dt Test Circuit

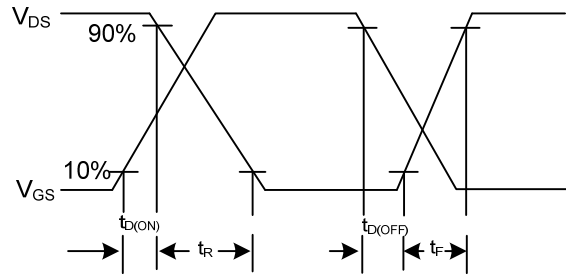


Peak Diode Recovery dv/dt Waveforms

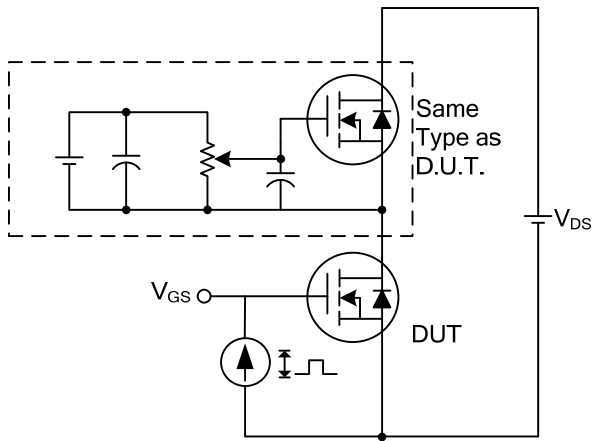
TEST CIRCUITS AND WAVEFORMS (Cont.)



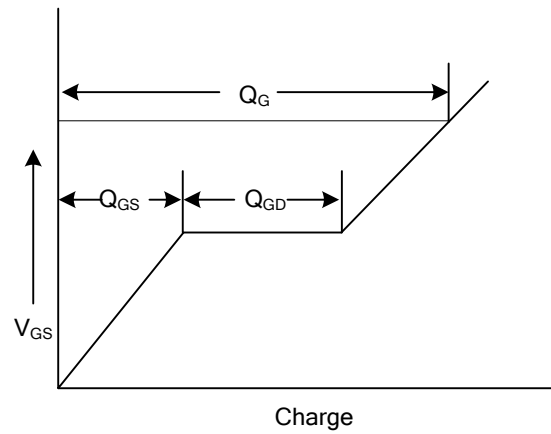
Switching Test Circuit



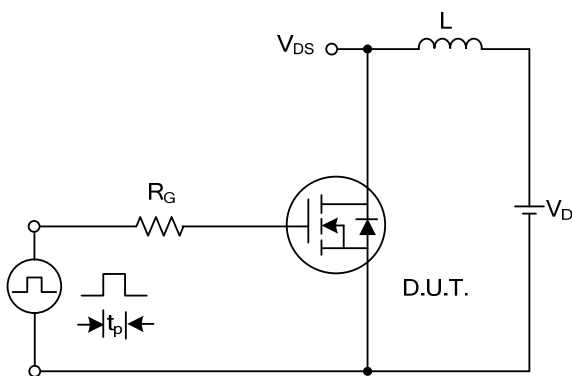
Switching Waveforms



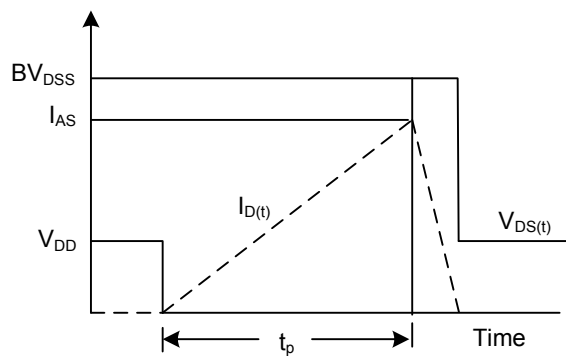
Gate Charge Test Circuit



Gate Charge Waveform

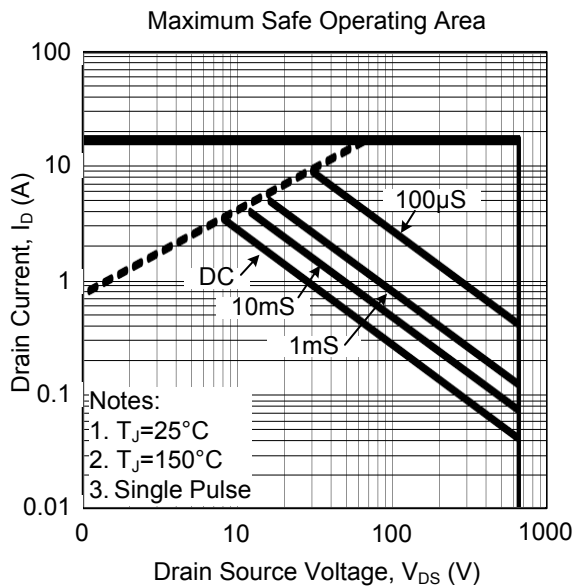
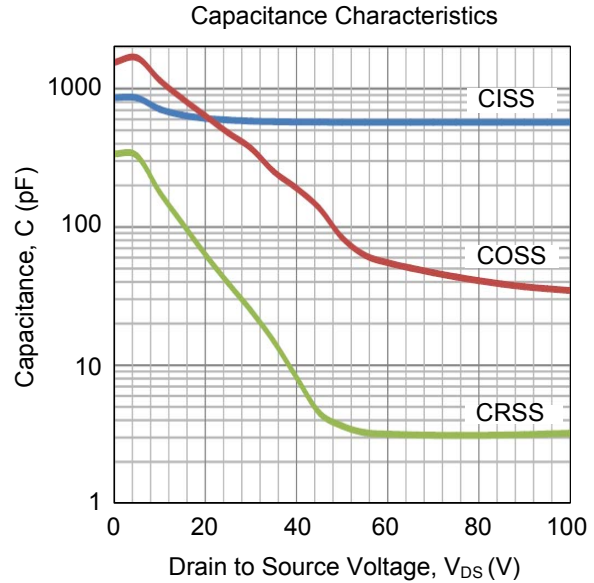
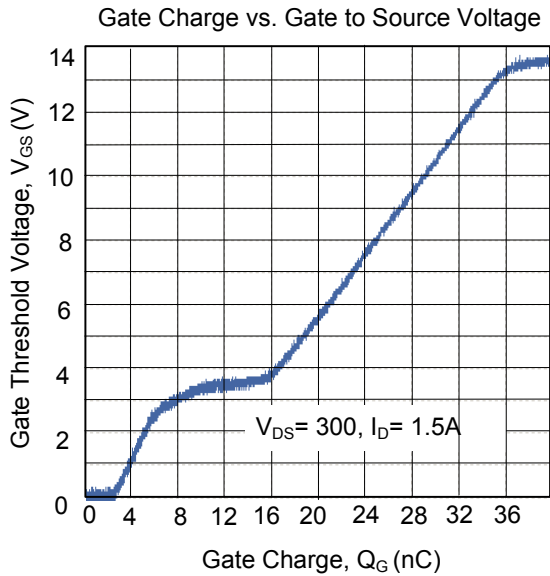


Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

TYPICAL CHARACTERISTICS



UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. UTC reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.